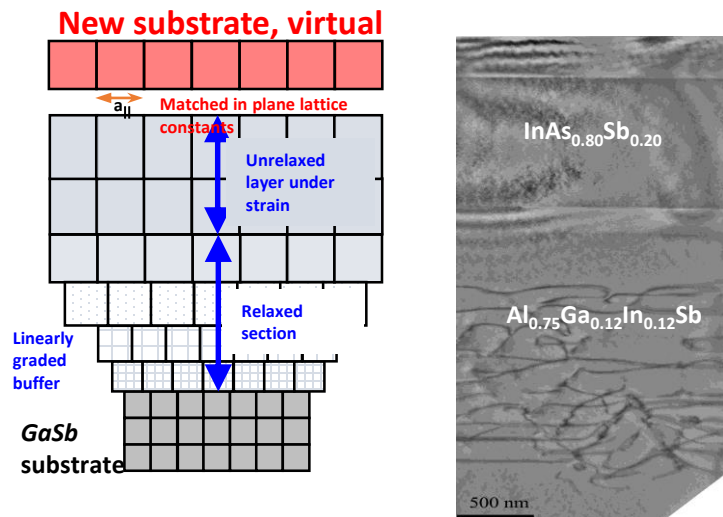


Development of the novel MBE materials for III-V IR optoelectronics

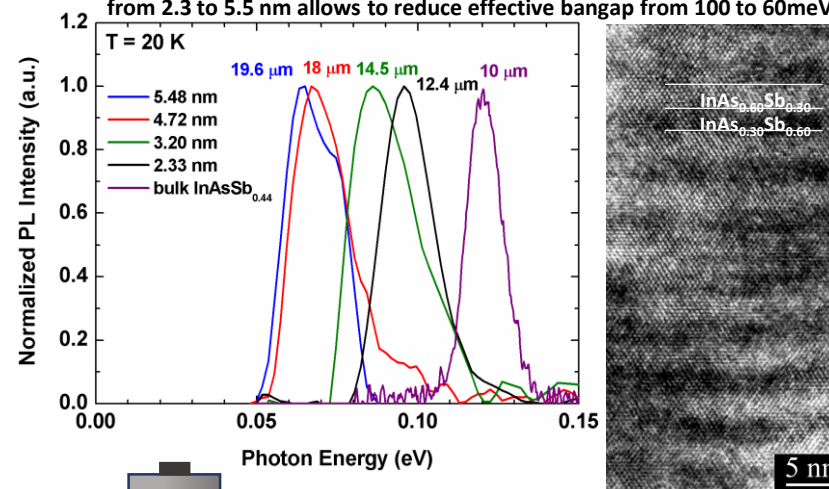
Novel Metamorphic Bulk InAsSb

New class of the semiconductor heterostructures for infrared photonics beyond **10 μm**



Novel Metamorphic periodic heterostructures operating up to **20 μm** wavelength

Changing the period of modulation, in InAsSb/InAsSb heterostructures, from 2.3 to 5.5 nm allows to reduce effective bandgap from 100 to 60 meV



In-situ control of crystal growth at the subnanometer scale

